



Description

The Advanced Ultra Low Power (AUP) CMOS logic family is designed for low power and extended battery life in portable applications.

The 74AUP2G126 is a dual 3-State Buffer. Each buffer has an individual output enable pin while asserted LOW will place the output in a high impedance state. The device is designed for operation over a power supply range of 0.8V to 3.6V. The device is fully specified for partial power down applications using IOFF. The IOFF circuitry disables the output preventing damaging current backflow when the device is powered down.

Features

- Advanced Ultra Low Power (AUP) CMOS
- Supply Voltage Range from 0.8V to 3.6V
- ±4mA Output Drive at 3.0V
- Low Static Power Consumption
- $I_{CC} < 0.9 \mu A$
- Low Dynamic Power Consumption
- C_{PD} = 6pF Typical at 3.6V
- Schmitt Trigger Action at All Inputs Make the Circuit Tolerant for Slower Input Rise and Fall Time. The hysteresis is typically 250mV at $V_{CC} = 3.0V$
- I_{OFF} Supports Partial-Power-Down Mode Operation
- ESD Protection per JESD 22
 - Exceeds 200-V Machine Model (A115)
 - Exceeds 2000-V Human Body Model (A114)
 - Exceeds 1000-V Charged Device Model (C101)
- Latch-Up Exceeds 100mA per JESD 78, Class I
- Leadless Packages per JESD30E
 - DFN1210 Denoted as X2-DFN1210-8
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Pin Assignments

(Top View)



X2-DFN1210-8

Applications

- Suited for Battery and Low Power Needs
- Wide Array of Products Such as:
 - Tablets, E-readers
 - Cell Phones, Personal Navigation / GPS
 - MP3 Players, Cameras, Video Recorders
 - PCs, Ultrabooks, Notebooks, Netbooks
 - Computer Peripherals, Hard Drives, SSD, CD/DVD ROM
 - TV, DVD, DVR, Set-Top Box

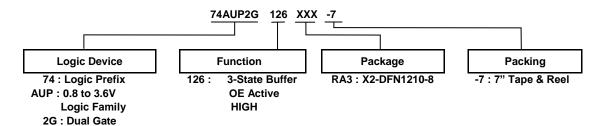
Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

1 of 11 74AUP2G126 January 2015 Document number: DS36145 Rev. 1 - 2 © Diodes Incorporated



Ordering Information



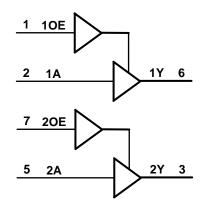
Device	Package	Package	Package	7" Tape and Reel			
Device	Code	(Notes 4, 5)	Size	Quantity	Part Number Suffix		
74AUP2G126RA3-7	RA3	X2-DFN1210-8	1.2mm X 1.0mm X 0.35mm 0.3mm Lead Pitch	5000/Tape & Reel	-7		

 Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf
 The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf Notes:

Pin Descriptions

Pin NO.	Pin Name	Description
1	10E	Output Enable Active HIGH
2	1A	Data Input
3	2Y	Data Output
4	GND	Ground
5	2A	Data Input
6	1Y	Data Output
7	20E	Output Enable Active HIGH
8	Vcc	Supply Voltage

Logic Diagram



Function Table

Inpu	Output						
OE	OE A						
Н	Н	Н					
Н	L	L					
L	X	Z					



Absolute Maximum Ratings (Notes 6, 7)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
V _{CC}	Supply Voltage Range	-0.5 to +4.6	V
VI	Input Voltage Range	-0.5 to +4.6	V
Vo	Voltage Applied to Output in High or Low State	-0.5 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current (V _I < 0)	50	mA
I _{OK}	Output Clamp Current (V _O < 0)	50	mA
Io	Continuous Output Current (V _O = 0 to V _{CC})	±20	mA
Icc	Continuous Current Through V _{CC}	50	mA
I _{GND}	Continuous Current Through GND	-50	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Notes:

- 6. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.
- 7. Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.

Recommended Operating Conditions (Note 8)

Symbol	Para	ameter	Min	Max	Unit
V_{CC}	Operating Voltage		0.8	3.6	V
VI	Input Voltage		0	3.6	V
Vo	Output Voltage		0	V _{CC}	V
		V _{CC} = 0.8V	_	-20	μΑ
		V _{CC} = 1.1V	_	-1.1	
	High Lovel Output Current	$V_{CC} = 1.4V$	_	-1.7	
Іон	High-Level Output Current	V _{CC} = 1.65V	_	-1.9	mA
		$V_{CC} = 2.3V$	_	-3.1	
		V _{CC} = 3.0V	_	-4	
		V _{CC} = 0.8V	_	20	μA
		V _{CC} = 1.1V	_	1.1	
	Love Lovel Output Current	$V_{CC} = 1.4V$	_	1.7	
l _{OL}	Low-Level Output Current	V _{CC} = 1.65V	_	1.9	mA
		$V_{CC} = 2.3V$	_	3.1	
		$V_{CC} = 3.0V$	_	4	
Δt/ΔV	Input Transition Rise or Fall Rate	V _{CC} = 0.8V to 3.6V	_	200	ns/V
T _A	Operating Free-Air Temperature		-40	+125	°C

Note: 8. Unused inputs should be held at $V_{\mbox{CC}}$ or Ground.



Electrical Characteristics

Cample of	Donomatan	Took Conditions	V	T _A = -	+25°C	T _A = -40°0	C to +85°C	11!4
Symbol	Parameter	Test Conditions	V _{CC}	Min	Max	Min	Max	Unit
		_	0.8V to 1.65V	0.80 X V _{CC}	_	0.80 X V _{CC}	_	
\/	High-Level Input	_	1.65V to 1.95V	0.65 X V _{CC}	_	0.65 X V _{CC}	_	V
V_{IH}	Voltage	_	2.3V to 2.7V	1.6	_	1.6	_	V
		_	3.0V to 3.6V	2.0	_	2.0	_	
		_	0.8V to 1.65V	_	0.30 X V _{CC}	_	0.30 X V _{CC}	
V_{IL}	Low-Level Input	_	1.65V to 1.95V	_	0.35 X V _{CC}	_	0.35 X V _{CC}	V
V IL	Voltage	_	2.3V to 2.7V	_	0.7	_	0.7	٠
		_	3.0V to 3.6V	_	0.9	_	0.9	
		I _{OH} = -20μA	0.8V to 3.6V	V _{CC} - 0.1	_	V _{CC} – 0.1	_	
		$I_{OH} = -1.1 \text{mA}$	1.1V	0.75 X V _{CC}	_	0.7 X V _{CC}	_	
	High-Level Output	$I_{OH} = -1.7 \text{mA}$	1.4V	1.11	_	1.03	_	
		I _{OH} = -1.9mA	1.65V	1.32	_	1.3	_	V
Vон	Voltage	I _{OH} = -2.3mA	0.01/	2.05	_	1.97	_	V
		I _{OH} = -3.1mA	2.3V	1.9	_	1.85	_	
		I _{OH} = -2.7mA	0)/	2.72	_	2.67	_	
		I _{OH} = -4mA	3V	2.6	_	2.55	_	
		I _{OL} = 20μA	0.8V to 3.6V	_	0.1	_	0.1	
		I _{OL} = 1.1mA	1.1V	_	0.3 X V _{CC}	_	0.3 X V _{CC}	
		I _{OL} = 1.7mA			0.31	_	0.37	
	Low-Level Output	I _{OL} = 1.9mA	1.65V	_	0.31	_	0.35	.,
V_{OL}	Voltage	I _{OL} = 2.3mA		_	0.31	_	0.33	V
		I _{OL} = 3.1mA	2.3V	_	0.44	_	0.45	
		I _{OL} = 2.7mA		_	0.31	_	0.33	
		I _{OL} = 4mA	3V	_	0.44	_	0.45	
lı	Input Current	A or B Input V _I = GND to 3.6V	0 to 3.6V	_	±0.1	_	±0.5	μΑ
l _{OZ}	Z-State Leakage Current	V_I or $V_O = 0V$ to 3.6V	0 to 3.6V	_	0.2	_	±0.5	μA
l _{OFF}	Power Down Leakage Current	V_I or $V_O = 0V$ to 3.6V	0V	_	±0.2	_	±0.5	μΑ
Δl _{OFF}	Delta Power Down Leakage Current	V_I or $V_O = 0V$ to 3.6V	0V to 0.2V	_	0.2	_	0.6	μΑ
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8V to 3.6V	_	0.5	_	0.9	μΑ
		Data Input at V_{CC} =0.6 V OE = GND, I_{O} = 0A	3.3V	_	40	_	50	μΑ
ΔI_{CC}	Additional Supply Current	OE Input at V_{CC} –0.6V Data Input = GND or V_{CC} , Io = 0A	3.3V	_	110	_	120	μΑ
		OE Input at VCC Data Input = GND to 3.6V, I _O = 0A	0.8V to 3.6V	_	1	_	1	μΑ



Electrical Characteristics (Cont.)

0	D	Tart Oan ditions	V	T _A = -40°C	to +125°C	1111	
Symbol	Parameter	Test Conditions	V _{CC}	Min	Max	Unit	
		_	0.8V to 1.65V	0.80 X V _{CC}	_		
\ <i>/</i>	High-Level Input	_	1.65V to 1.95V	0.70 X V _{CC}	_		
V_{IH}	Voltage	_	2.3V to 2.7V	1.6	_	v	
		_	3.0V to 3.6V	2.0	_		
		_	0.8V to 1.65V	_	0.25 X V _{CC}		
VIL	Low-Level Input	_	1.65V to 1.95V	_	0.30 X V _{CC}	V	
VIL	Voltage	_	2.3V to 2.7V	_	0.7	V	
		_	3.0V to 3.6V		0.9		
		$I_{OH} = -20\mu A$	0.8V to 3.6V	V _{CC} – 0.11	_		
		I _{OH} = -1.1mA	1.1V	0.6 X V _{CC}	_		
		$I_{OH} = -1.7 \text{mA}$	1.4V	0.93	_		
	High-Level Output	I _{OH} = -1.9mA	1.65V	1.17	_		
Vон	Voltage	I _{OH} = -2.3mA	0.01/	1.77	_		
		I _{OH} = -3.1mA	2.3V	1.67	_		
		I _{OH} = -2.7mA	2) /	2.40	_		
		I _{OH} = -4mA	3V	2.30	_		
		I _{OL} = 20μA	0.8V to 3.6V	_	0.11		
		I _{OL} = 1.1mA	1.1V	_	0.33 X V _{CC}		
		I _{OL} = 1.7mA	1.4V	_	0.41		
	Low-Level Output	I _{OL} = 1.9mA	1.65V	_	0.39	_	
V_{OL}	Voltage	I _{OL} = 2.3mA		_	0.36	V	
		I _{OL} = 3.1mA	2.3V	_	0.50		
		I _{OL} = 2.7mA		_	0.36		
		I _{OL} = 4mA	3V	_	0.50		
II	Input Current	A or B Input, V _I = GND to 3.6V	0 to 3.6V	_	±0.75	μA	
loz	Z-State Leakage Current	V_1 or $V_0 = 0V$ to 3.6V	0 to 3.6V	_	±1.5	μΑ	
l _{OFF}	Power Down Leakage Current	V _I or V _O = 0V to 3.6V	0	_	±3.5	μΑ	
ΔI_{OFF}	Delta Power Down Leakage Current	V_I or $V_O = 0V$ to 3.6V	0V to 0.2V	_	±2.5	μΑ	
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8V to 3.6V	_	3.0	μA	
		Data Input at V _{CC} -0.6V OE = GND, I _O =0A	3.3V	_	75	μА	
Δlcc	Additional Supply Current	OE Input at V _{CC} -0.6V Data Input = GND or V _{CC} , I _O =0A	3.3V	_	180	μА	
		OE Input at VCC Data Input = GND to 3.6V, I _O = 0A	0.8V to 3.6V	-	1	μА	



Operating and Package Characteristics (@T_A = +25°C, unless otherwise specified.)

	Parameter	Test Condition	ns	Vcc	Тур	Unit
				0.8V	6.5	
				1.2V ± 0.1V	6.3	
	Power Dissipation	f = 1MHz Output Enabled		1.5V ± 0.1V	6.3	
C _{PD}	Capacitance per Gate	No Load		1.8V ± 0.15V	6.2	pF
		2.5V ± 0.2V	2.5V ± 0.2V	6.2		
				3.3V ± 0.3V	6.1	
Cı	Input Capacitance	$V_I = V_{CC}$ or GND	V _I = V _{CC} or GND		1.5	pF
		Output Enabled Vo =	GND	0V	2.9	pF
Co	Output Capacitance	Output Disabled V _O = V _{CC}	= GND or	0V or 3.6V	2.1	pF
θја	Thermal Resistance Junction-to-Ambient	X2-DFN1210-8	(Note 9)	_	395	°C/W
θιс	Thermal Resistance Junction-to-Case	X2-DFN1210-8	(Note 9)	_	236	°C/W

Note: 9. Test condition, X2-DFN1210-8 device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



Switching Characteristics

 $C_L = 5pF$ see Figure 1

Davamatan	From	То	V		T _A = +25°C	;	$T_A = -40^{\circ}C$	C to +85°C	$T_A = -40^{\circ}C$	to +125°C	l lm!4					
Parameter	Input	Output	V _{CC}	Min	Тур	Max	Min	Max	Min	Max	Unit					
		V8.0	_	20.6	_	_	_	_	_							
			1.2V ± 0.1V	2.8	5.5	12.6	2.5	14	2.5	17						
	Α	Y	1.5V ± 0.1V	2.2	3.9	7.3	2.0	7.6	2.0	8.1	ns					
t _{PD}	А	ĭ	1.8V ± 0.15V	1.9	3.2	4.1	1.7	6.1	1.7	6.7						
			2.5V ± 0.2V	1.6	2.6	3.6	1.4	4.3	1.4	4.9						
			$3.3V \pm 0.3V$	1.4	2.4	3.1	1.2	3.9	1.2	4.4						
				V8.0	_	71.6	_	_	_	_	_					
			1.2V ± 0.1V	2.8	6.2	14.9	2.6	19.6	2.6	19.8						
		Y	1.5V ± 0.1V	2.3	4.2	8.3	2.2	8.8	2.2	9.2						
t _{EN}	OE	OE	OE	OE	ŌE	OE	ĭ	1.8V ± 0.15V	1.9	3.3	6.4	1.7	7.1	1.7	7.4	ns
			2.5V ± 0.2V	1.5	2.4	4.3	1.4	4.6	1.4	4.9						
			3.3V ± 0.3V	1.3	2.0	3.8	1.2	4.2	1.2	4.4						
			V8.0	_	10.3	_	_	_	_	_						
			1.2V ± 0.1V	2.6	4.2	8.9	2.9	9.2	2.9	9.4						
	OE Y	V	1.5V ± 0.1V	2.1	3.2	6.4	2.2	6.6	2.2	6.7						
t _{DIS}		1.8V ± 0.15V	2.1	3.1	5.6	1.7	5.8	1.7	6.1	ns						
		2.5V ± 0.2V 1.7 2.4 4.0 1.4 4.3 1.4	1.4	4.5	1											
			3.3V ± 0.3V	2.1	2.8	4.9	1.2	5.0	1.2	5.1						

C_L = 10pF see Figure 1

Parameter	From	То	V		T _A = +25°C	;	$T_A = -40^{\circ}C$	C to +85°C	$T_A = -40^{\circ}C$	to +125°C	Unit				
Parameter	Input	Output	V _{CC}	Min	Тур	Max	Min	Max	Min	Max	Offic				
			V8.0	_	24.0	_	_	_	_	_					
			1.2V ± 0.1V	3.2	6.4	14.8	3.0	16.6	3.0	18.3					
	Α	Y	1.5V ± 0.1V	2.1	4.5	8.8	1.9	9.1	1.9	9.4	20				
t _{PD}	A	l i	1.8V ± 0.15V	1.9	3.8	5.5	1.7	6.8	1.7	7.6	ns				
			2.5V ± 0.2V	2.1	3.2	4.2	1.6	5.3	1.6	5.9					
			$3.3V \pm 0.3V$	1.8	3.0	3.8	1.6	4.6	1.6	5.2	<u> </u>				
			0.8V	_	75.3	_	_	_	_	_					
			1.2V ± 0.1V	3.2	7.1	16.9	3.0	22.2	3.0	22.4					
	ŌĒ	Y	1.5V ± 0.1V	2.2	4.8	9.6	2.1	10.0	2.1	10.3	ns				
t _{EN}	OE	l i	1.8V ± 0.15V	1.8	3.9	7.1	1.7	7.8	1.7	8.2	115				
			2.5V ± 0.2V	1.5	2.9	5.0	1.4	5.4	1.4	5.8					
			$3.3V \pm 0.3V$	1.4	2.6	4.7	1.3	4.9	1.3	5.2					
			V8.0	_	12.2	_	_	_	_	_					
			1.2V ± 0.1V	3.5	5.3	10.9	3.3	11.4	3.3	11.6					
	OE Y		1.5V ± 0.1V	2.2	4.1	8.0	2.1	8.2	2.1	8.5	20				
t _{DIS}		1.8V ± 0.15V	2.4	4.2	7.1	1.7	7.4	1.7	7.6	ns					
		2.5V ± 0.2V	1.9	3.2	5.1	1.4	5.5	1.4	5.7						
			$3.3V \pm 0.3V$	2.4	4.1	6.8	1.3	7.1	1.3	7.2					



Switching Characteristics (Cont.)

C_L = 15pF see Figure 1

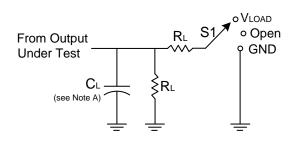
Parameter	From	То	V		T _A = +25°C	;	T _A = -40°C	C to +85°C	T _A = -40°C	to +125°C	Unit				
Parameter	Input	Output	Vcc	Min	Тур	Max	Min	Max	Min	Max	Unit				
			0.8V	_	27.4	_	_	_	_	_					
			1.2V ± 0.1V	3.6	7.2	15.5	3.3	22.4	3.3	22.5					
	Α	Y	1.5V ± 0.1V	3.0	5.1	8.8	2.5	9.8	2.5	10.9					
t _{PD}	А	Y	1.8V ± 0.15V	2.2	4.3	6.3	2.0	7.9	2.0	8.8	ns				
			2.5V ± 0.2V	2.0	3.7	4.9	1.8	6.0	1.8	6.7					
			$3.3V \pm 0.3V$	2.0	3.5	4.4	1.8	5.4	1.8	6.1					
			0.8V	_	79.2	_	_	_	_	_					
			1.2V ± 0.1V	3.6	7.8	19.0	3.3	21.8	3.3	22					
		Y	1.5V ± 0.1V	3.0	5.4	10.6	2.9	11.3	2.9	11.6	20				
t _{EN}	OE	OE	ŌĒ	r	1.8V ± 0.15V	2.1	4.3	8.0	2.0	8.8	2.0	9.2	ns		
			2.5V ± 0.2V	1.8	3.4	5.8	1.7	6.2	1.7	6.7					
			$3.3V \pm 0.3V$	1.6	3.1	5.3	1.5	5.9	1.5	6.1					
			0.8V	_	14.9	_	_	_	_	_					
			1.2V ± 0.1V	4.3	6.4	13.9	3.7	15.5	3.7	15.7					
		Y 1	1.5V ± 0.1V	3.0	5.0	8.8	2.5	9.7	2.5	9.9					
t _{DIS}	ŌĒ		1.8V ± 0.15V	3.1	5.4	8.8	2.0	10.3	2.0	10.5	ns				
			2.5V ± 0.2V	2.4	4.0	8.2	1.7	8.4	1.7	8.6					
			$3.3V \pm 0.3V$	3.2	5.3	8.6	1.5	9.2	1.5	9.4					

$C_L = 30pF$ see Figure 1

Daramatar	From	То	. v		T _A = +25°C	;	$T_A = -40^{\circ}$	C to +85°C	$T_A = -40^{\circ}C$	to +125°C	Unit			
Parameter	Input	Output	V _{CC}	Min	Тур	Max	Min	Max	Min	Max	Onit			
		V8.0	_	37.4	_	_	_	_	_					
			1.2V ± 0.1V	4.8	9.5	20.7	4.4	27.6	4.4	27.8				
	Α	Y	1.5V ± 0.1V	4.0	6.7	10.8	3.0	13.0	3.0	14.5	ns			
t _{PD}	А	Y	1.8V ± 0.15V	2.9	5.6	8.4	2.6	10.3	2.6	11.5				
			2.5V ± 0.2V	2.7	4.8	6.3	2.5	7.8	2.5	8.7				
			$3.3V \pm 0.3V$	2.7	4.6	5.8	2.5	7.0	2.5	8.3				
				V8.0	_	90.6	_	_	_	_	_			
			1.2V ± 0.1V	4.7	10.0	24.5	4.3	26.4	4.3	26.6	ns			
		Y	1.5V ± 0.1V	3.0	6.9	13.6	3.7	14.4	3.7	15.0				
t _{EN}	ŌĒ	ī	1.8V ± 0.15V	2.6	5.6	10.3	3.2	11.4	3.2	12.1				
			2.5V ± 0.2V	2.3	4.5	7.6	2.9	8.2	2.9	8.8				
			$3.3V \pm 0.3V$	2.2	4.2	7.5	2.7	8.3	2.7	8.7				
			V8.0		51.6	_	_	_	_	_				
			1.2V ± 0.1V	6.0	9.8	16.3	4.7	18.7	4.7	18.9				
	obs OE Y	1.5V ± 0.1V	4.5	7.7	12.6	3.0	12.8	3.0	13.2	no				
IDIS		1.8V ± 0.15V	5.2	8.8	13.7	2.6	13.8	2.6	13.9	ns				
			2.5V ± 0.2V	3.9	6.4	8.9	2.3	10.8	2.3	12.2				
			3.3V ± 0.3V	5.5	9.0	13.9	2.2	14.0	2.2	15.6				

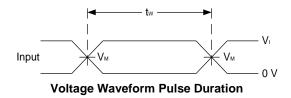


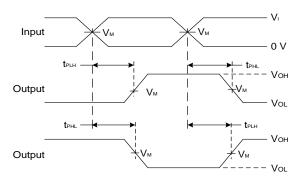
Parameter Measurement Information

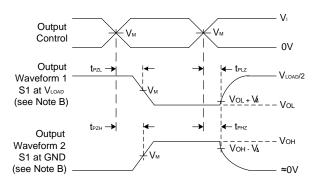


TEST	S1	R_{L}
t _{PLH} /t _{PHL}	Open	1ΜΩ
t _{PLZ} /t _{PZL}	V_{LOAD}	5ΚΩ
t _{PHZ} /t _{PZH}	GND	5ΚΩ

.,	In	puts		•	WA	
Vcc	VI	t _r /t _f	V _M	V _{LOAD}	CL	V Δ
0.8V	V _{CC}	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.1V
1.2V±0.1V	V _{CC}	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.1V
1.5V±0.1V	Vcc	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.1V
1.8V±0.15V	V _{CC}	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.15V
2.5V±0.2V	Vcc	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.15V
3.3V±0.3V	Vcc	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.3V







Voltage Waveform Enable and Disable Times Low and High Level Enabling

Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Figure 1. Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

- B. All pulses are supplied at pulse repetition rate \leq 10MHz.
- C. Inputs are measured separately one transition per measurement.
- D. t_{PLZ} and t_{PHZ} are the same as t_{DIS}.
- E. t_{PZL} and t_{PZH} are the same as $t_{\text{EN.}}$
- F. t_{PLH} and t_{PHL} are the same as t_{PD}.



Marking Information

X2-DFN1210-8

(Top View)

 \underline{XX} : Identification Code

Y : Year : 0~9

W : Week : A~Z : 1~26 Week

a~z: 27-52 Week

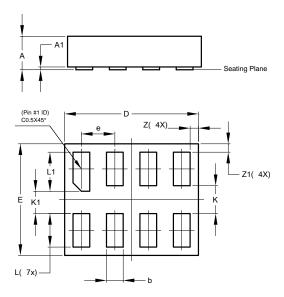
z Represents 52 and 53 Week

X: Week: A~Z: Internal Code

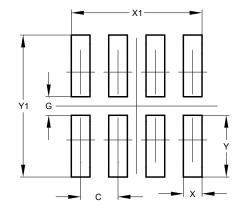
Part Number	Package	Identification Code	
74AUP2G126RA3-7	X2-DFN1210-8	KT	

X2-DFN1210-8 Package Outline Dimensions and Suggested Pad Layout

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



X2-DFN1210-8				
Dim	Min	Max	Тур	
Α	-	0.35	0.30	
A 1	0	0.03	0.02	
b	0.10	0.20	0.15	
D	1.15	1.25	1.20	
Е	0.95	1.05	1.00	
е	-	-	0.30	
K	-	-	0.25	
K 1	-	-	0.20	
L	0.25	0.35	0.30	
L1	0.30	0.40	0.35	
Z	0.050	0.100	0.075	
Z 1	0.050	0.100	0.075	
All Dimensions in mm				



Dimensions	Value (in mm)
С	0.300
G	0.150
Х	0.150
X1	1.050
Y	0.500
V1	1 150



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